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50 V, single P-channel Trench MOSFET Rev. 1 — 6 June 2012

Product data sheet

1. **Product profile**

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver

1.4 Quick reference data

- ElectroStatic Discharge (ESD) protection up to 1 kV
- Ultra thin package profile with 0.37 mm height
- High-side load switch
- Switching circuits

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-50	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V_{GS} = -10 V; T_{amb} = 25 °C	<u>[1]</u>	-	-	-230	mA
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -100 mA; T_j = 25 °C		-	4.5	7.5	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



50 V, single P-channel Trench MOSFET

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	S	source		
3	D	drain	2 Transparent top view SOT883B (DFN1006B-3)	G S 017aaa259

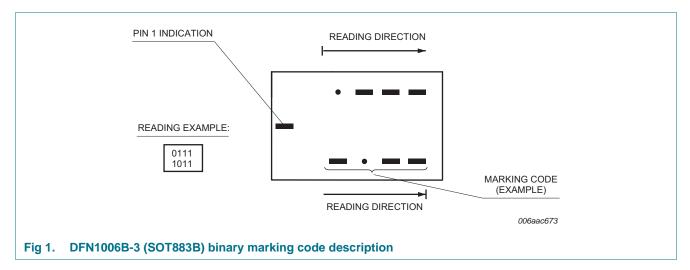
3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
BSS84AKMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body $1.0 \times 0.6 \times 0.37$ mm	SOT883B		

4. Marking

Table 4. Marking codes

Type number	Marking code
BSS84AKMB	0000 0010



50 V, single P-channel Trench MOSFET

5. Limiting values

Table 5. Limiting values

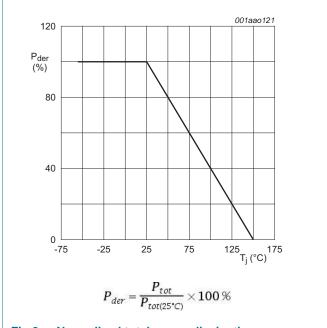
In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
drain-source voltage			-	-50	V
gate-source voltage	_ ;		-20	20	V
drain current	V _{GS} = -10 V; T _{amb} = 25 °C	<u>[1]</u>	-	-230	mA
	V _{GS} = -10 V; T _{amb} = 100 °C	<u>[1]</u>	-	-150	mA
peak drain current	$T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \mu\text{s}$		-	-0.9	А
total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW
		[1]	-	715	mW
	T _{sp} = 25 °C		-	2700	mW
junction temperature			-55	150	°C
ambient temperature			-55	150	°C
storage temperature			-65	150	°C
liode					
source current	T _{amb} = 25 °C	<u>[1]</u>	-	-230	mA
n rating					
electrostatic discharge voltage	HBM	[3]	-	1000	V
	gate-source voltage drain current peak drain current total power dissipation junction temperature ambient temperature storage temperature liode source current rating	gate-source voltagedrain current $V_{GS} = -10 \text{ V}; \text{ T}_{amb} = 25 ^{\circ}\text{C}$ $V_{GS} = -10 \text{ V}; \text{ T}_{amb} = 100 ^{\circ}\text{C}$ peak drain current $T_{amb} = 25 ^{\circ}\text{C}; \text{ single pulse; } t_p \le 10 \ \mu\text{s}$ total power dissipation $T_{amb} = 25 ^{\circ}\text{C}$ junction temperatureambient temperaturestorage temperaturesource current $T_{amb} = 25 ^{\circ}\text{C}$ rating	gate-source voltagedrain current $V_{GS} = -10 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$ [1] $V_{GS} = -10 \text{ V}; T_{amb} = 100 ^{\circ}\text{C}$ [1]peak drain current $T_{amb} = 25 ^{\circ}\text{C};$ single pulse; $t_p \le 10 \text{ µs}$ total power dissipation $T_{amb} = 25 ^{\circ}\text{C}$ [2]junction temperature[1]ambient temperatureImage: Colored state storage temperaturestorage temperatureImage: Colored state storage temperaturesource current $T_{amb} = 25 ^{\circ}\text{C}$ findeImage: Colored state storage temperaturesource current $T_{amb} = 25 ^{\circ}\text{C}$ findeImage: Colored state storage temperaturesource currentTamb = 25 ^{\circ}\text{C}findeImage: Colored state storage temperaturefindeImage: Colored storage temperaturefindeImage: Colored storage temperaturefindeImage: Colored storage temperaturefindeImage: Colored storage temperaturefindeI	gate-source voltage-20drain current $V_{GS} = -10 \text{ V}; T_{amb} = 25 ^{\circ} \text{C}$ [1]- $V_{GS} = -10 \text{ V}; T_{amb} = 100 ^{\circ} \text{C}$ [1]-peak drain current $T_{amb} = 25 ^{\circ} \text{C};$ single pulse; $t_p \le 10 \ \mu\text{s}$ -total power dissipation $T_{amb} = 25 ^{\circ} \text{C}$ [2]- $T_{amb} = 25 ^{\circ} \text{C}$ [1]-junction temperature-55ambient temperature-55storage temperature-55source current $T_{amb} = 25 ^{\circ} \text{C}$ -65source current $T_{amb} = 25 ^{\circ} \text{C}$ 1]total power dissipation- $T_{amb} = 25 ^{\circ} \text{C}$ -junction temperature-55ambient temperature-55storage temperature-65source current $T_{amb} = 25 ^{\circ} \text{C}$ 1]traing-	gate-source voltage -20 20 drain current $V_{GS} = -10 \ V; \ T_{amb} = 25 \ ^{\circ}C$ [1] - -230 $V_{GS} = -10 \ V; \ T_{amb} = 100 \ ^{\circ}C$ [1] - -150 peak drain current $T_{amb} = 25 \ ^{\circ}C; \ single pulse; \ t_p \le 10 \ \mu s$ - -0.9 total power dissipation $T_{amb} = 25 \ ^{\circ}C$ [2] - 360 junction temperature - - 2700 junction temperature - - - 2700 storage temperature - - - 55 150 storage temperature -

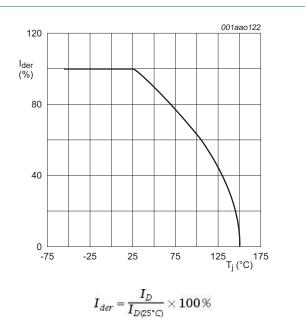
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.



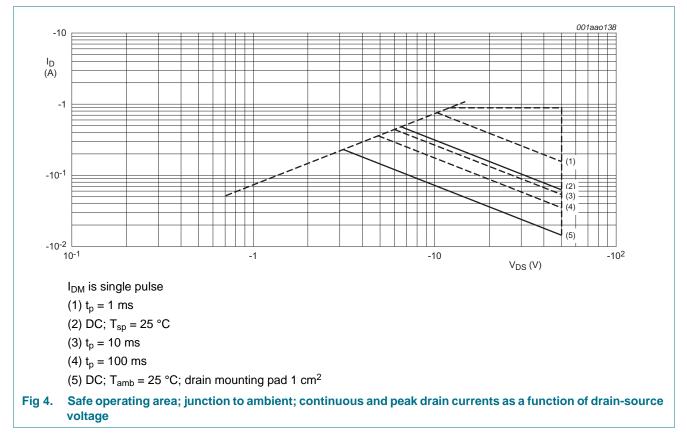






BSS84AKMB

50 V, single P-channel Trench MOSFET



6. Thermal characteristics

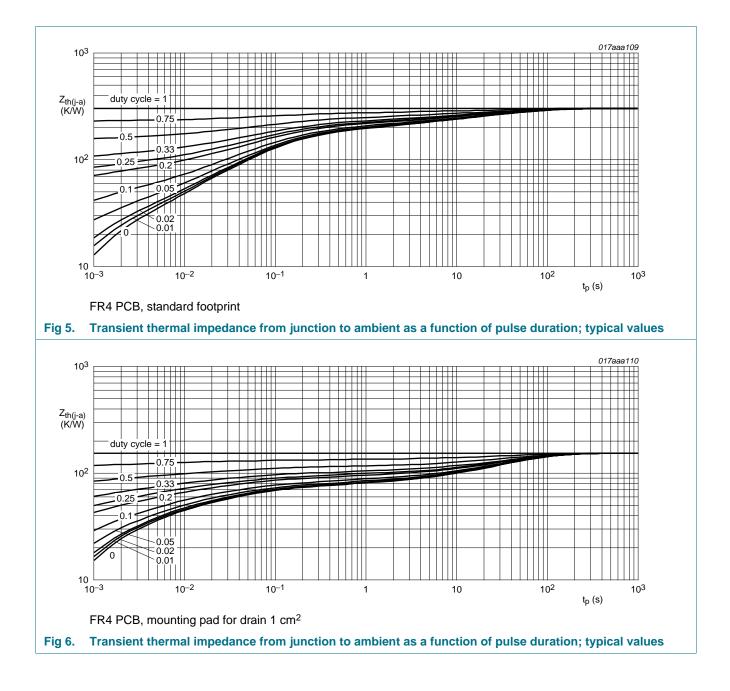
Table 6. **Thermal characteristics** Symbol Parameter Conditions Min Max Unit Typ thermal resistance in free air [1] 305 350 K/W R_{th(j-a)} from junction to [2] K/W 150 175 ambient thermal resistance 40 K/W R_{th(j-sp)} _ from junction to solder point

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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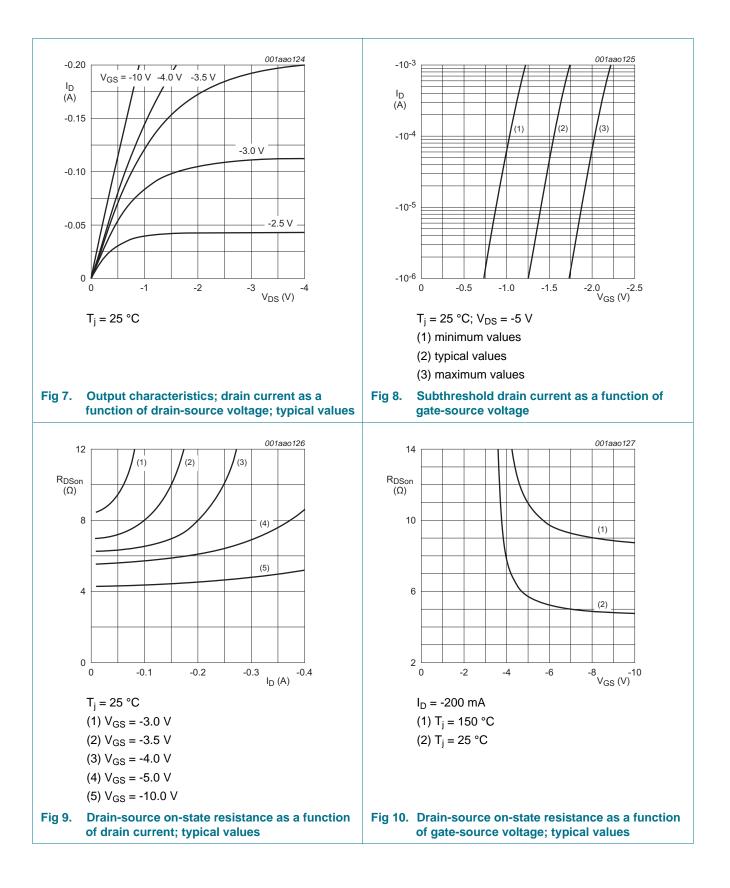


50 V, single P-channel Trench MOSFET

7. Characteristics

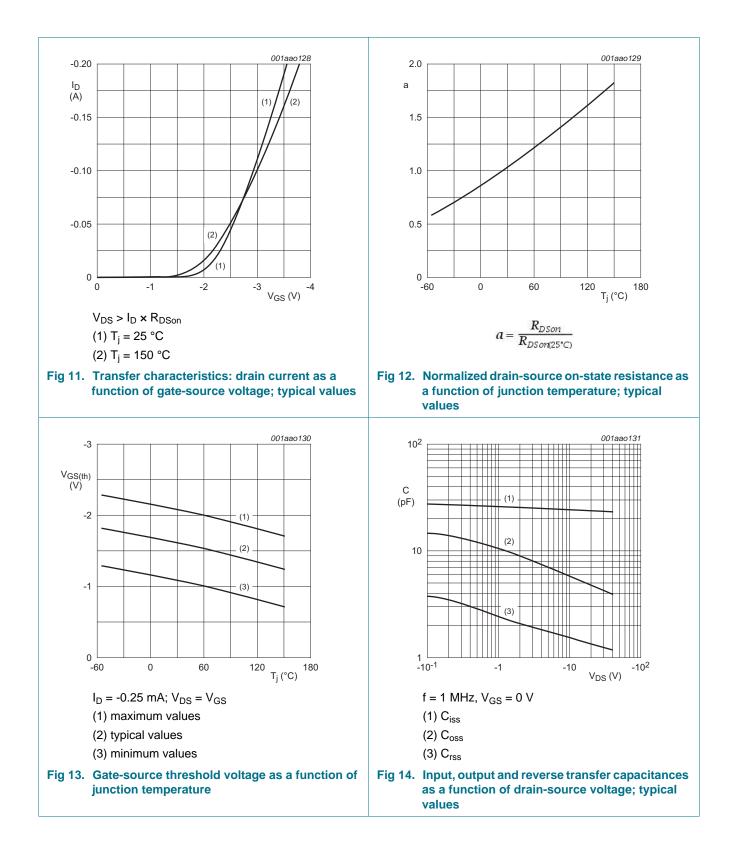
Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \ \mu A; V_{GS} = 0 \ V; T_j = 25 \ ^{\circ}C$	-50	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	-1.1	-1.6	-2.1	V
I _{DSS}	drain leakage current	V _{DS} = -50 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μA
		$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; \text{ T}_{j} = 150 \text{ °C}$	-	-	-2	μA
I _{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	-	-10	μA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μA
R _{DSon}	drain-source on-state	V_{GS} = -10 V; I _D = -100 mA; T _j = 25 °C	-	4.5	7.5	Ω
	resistance	V _{GS} = -10 V; I _D = -100 mA; T _j = 150 °C	-	8	13.5	Ω
		V_{GS} = -5 V; I_{D} = -100 mA; T_{j} = 25 °C	-	5.7	8.5	Ω
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -100 mA; T_j = 25 °C	-	150	-	mS
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -25 V; I_{D} = -200 mA; V_{GS} = -5 V;	-	0.26	0.35	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q_{GD}	gate-drain charge	V_{DS} = -10 V; I_{D} = -200 mA; V_{GS} = -5 V; T_{j} = 25 °C	-	0.09	-	nC
C _{iss}	input capacitance	V_{DS} = -25 V; f = 1 MHz; V_{GS} = 0 V;	-	24	36	pF
C _{oss}	output capacitance	T _j = 25 °C	-	4.5	-	pF
C _{rss}	reverse transfer capacitance		-	1.3	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -30 V; R_{L} = 250 Ω ; V_{GS} = -10 V;	-	13	26	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	11	-	ns
t _{d(off)}	turn-off delay time		-	48	96	ns
t _f	fall time		-	25	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	I _S = -115 mA; V _{GS} = 0 V; T _i = 25 °C	-0.48	-0.85	-1.2	V

50 V, single P-channel Trench MOSFET



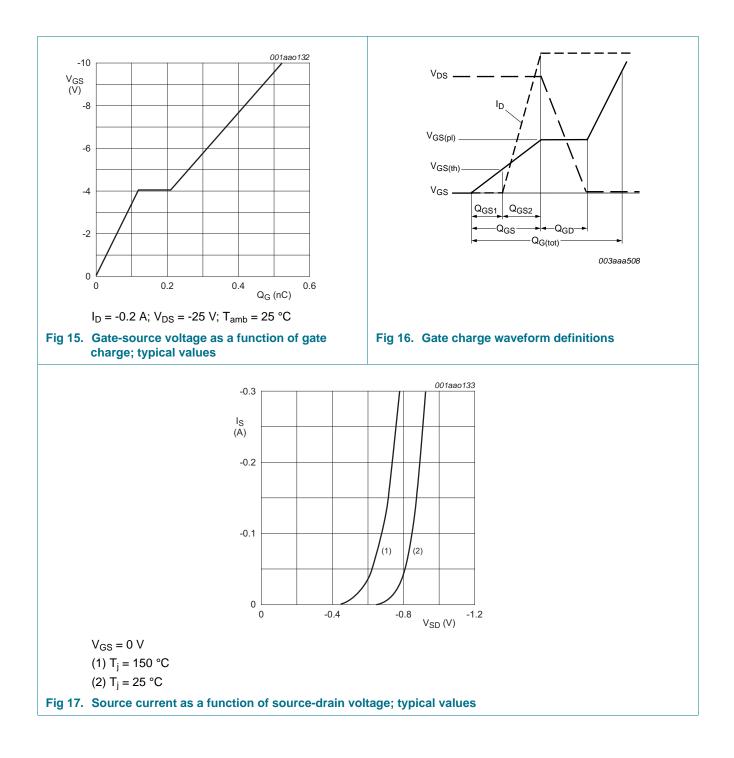
BSS84AKMB

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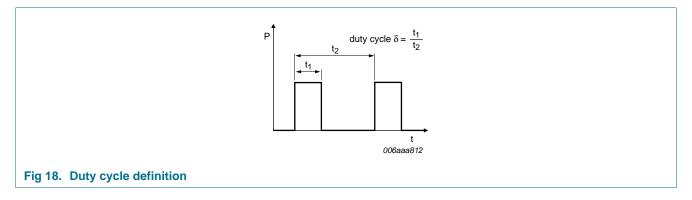
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50 V, single P-channel Trench MOSFET

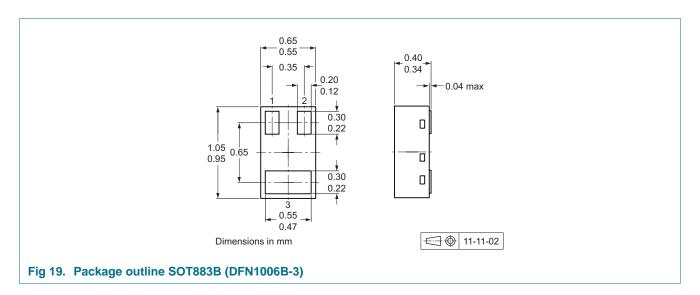


50 V, single P-channel Trench MOSFET

8. Test information

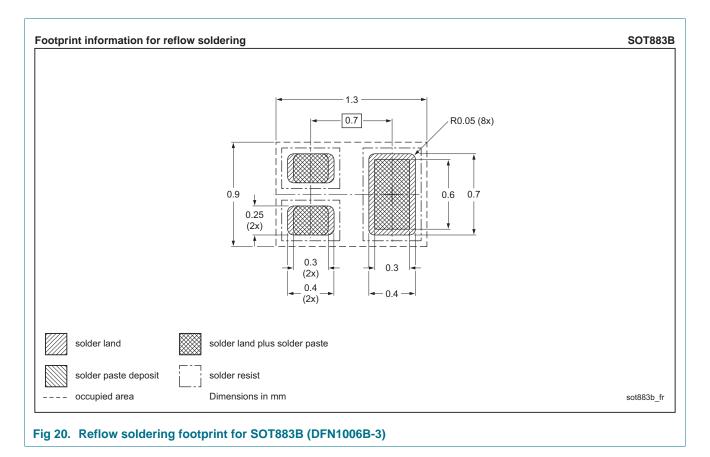


9. Package outline



50 V, single P-channel Trench MOSFET

10. Soldering



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11. Revision history

Table 8.	8. Revision history				
Document	ID	Release date	Data sheet status	Change notice	Supersedes
BSS84AKM	B v.1	20120606	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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